



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
001/	65mΩ @ V _{GS} = -10V	-3.8A
-30V	99mΩ @ V _{GS} = -4.5V	-3.0A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

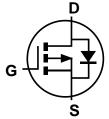
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)

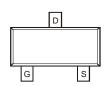
SOT23



Top View



Equivalent Circuit



Top View Pin Configuration

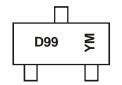
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3099LQ-7	SOT23	3000/Tape & Reel
DMP3099LQ-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D99 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Date Code Rey												
Year	2016	i	2017	2018	3	2019	2020)	2021	2022	2	2023
Code	D		E	F		G	Н			J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteris	tic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 6) V _{GS} = -10V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-3.8 -2.9	А	
Pulsed Drain Current (Note 7)			I _{DM}	-11	A
Avalanche Current, L = 0.1mH			las	-14.3	A
Avalanche Energy, L = 0.1mH			E _{AS}	10.2	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	1.08	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	$R_{\theta JA}$	115	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C

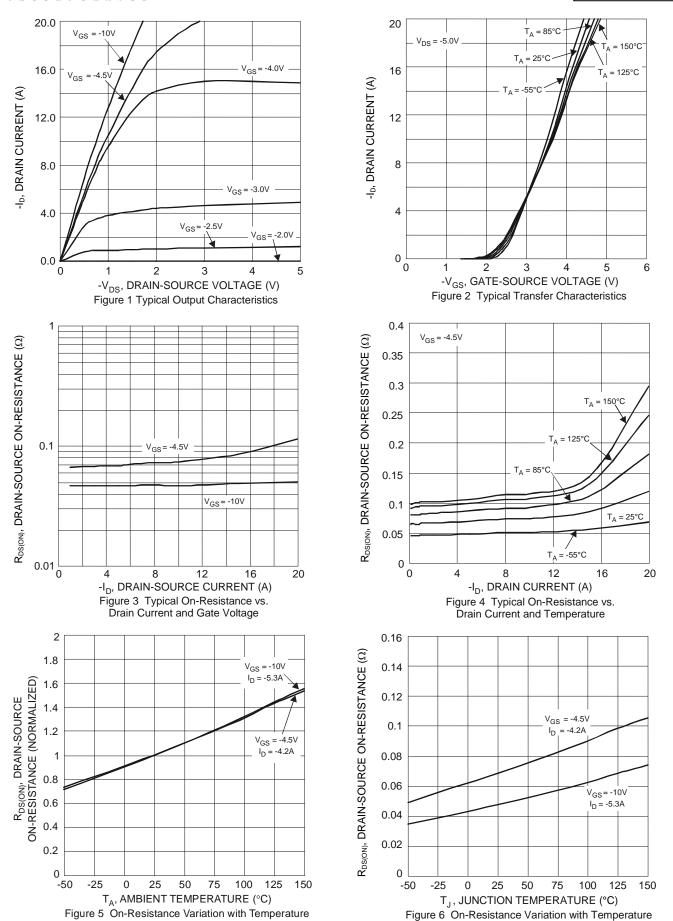
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-800	nA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0		-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D			65	mΩ	$V_{GS} = -10V, I_D = -3.8A$	
Static Drain-Source Off-Resistance	R _{DS(ON)}		_	99	11122	$V_{GS} = -4.5V$, $I_D = -3.0A$	
Forward Transfer Admittance	Y _{fs}	1	3.6	_	S	$V_{DS} = -5V, I_{D} = -2.7A$	
Diode Forward Voltage	V _{SD}	_	_	-1.26	V	$V_{GS} = 0V, I_{S} = -2.7A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		563	_	pF	.,	
Output Capacitance	Coss		48	_	pF	$V_{DS} = -25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	41	_	pF		
Gate Resistance	R _G		10.3	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Q_{g}	_	5.2	_		$V_{DS} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -3.8A$	
		ı	11	_	nC	15)/)/ 10)/	
Gate-Source Charge	Q_{gs}		1.7	_		$V_{DS} = -15V, V_{GS} = -10V,$	
Gate-Drain Charge	Q_{gd}	_	1.9	_		$I_D = -3.8A$	
Turn-On Delay Time	t _{D(ON)}	_	4.8	_			
Rise Time	t _R	_	5.0	_	no	$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}		31		ns	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t _F	_	15				

Notes:

- 6. Device mounted on FR-4 PCB on 2 oz., 0.5 inch² copper pads and $t \le 5$ sec.
- 7. Pulse width ≤10µs, Duty Cycle ≤1%.
- 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.







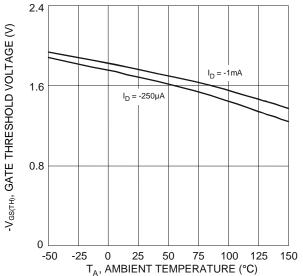
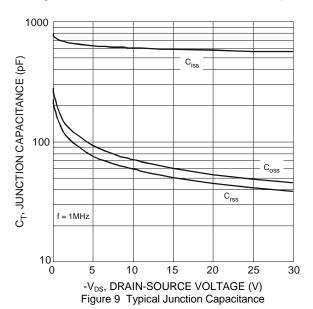


Figure 7 Gate Threshold Variation vs. Ambient Temperature



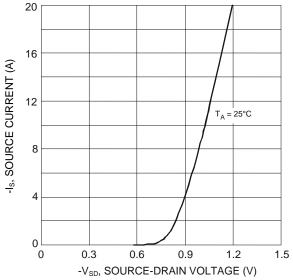
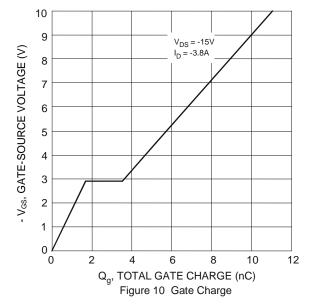


Figure 8 Diode Forward Voltage vs. Current

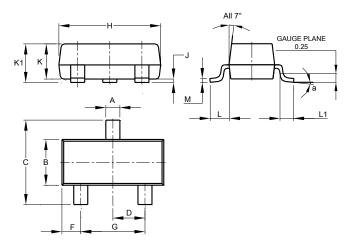




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

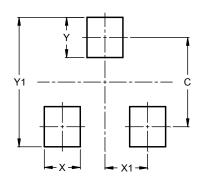


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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